

Please add the following new claims:

Q' --13. An input/output protection device in accordance with claim 3, wherein the third diffusion layer has a depth equal to or more than that of the fourth diffusion layer.

14. An input/output protection device in accordance with claim 2, wherein a lateral, bipolar transistor including the first diffusion layer as a collector, the second and third diffusion layers as an emitter, and the region of the first conduction type or the fourth diffusion layer as a base is put to operation.

15. An input/output protection device in accordance with claim 3, wherein a lateral, bipolar transistor including the first diffusion layer as a collector, the second and third diffusion layers as an emitter, and the region of the first conduction type or the fourth diffusion layer as a base is put to operation.

16. An input/output protection device in accordance with claim 4, wherein a lateral, bipolar transistor including the first diffusion layer as a collector, the second and third diffusion layers as an emitter, and the region of the first conduction type or the fourth diffusion layer as a base is put to operation.

17. An input/output protection device in accordance with claim 2, wherein the first and second diffusion layers are isolated from each other by a device separating isolation layer on a surface of the semiconductor substrate.

09619669-071900